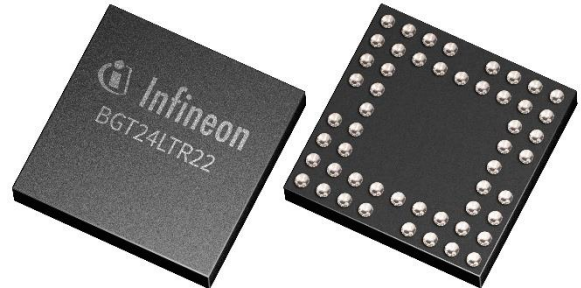


BGT24LTR22

Low Power Multichannel 24GHz Radar MMIC for Smart Sensing Applications

Features

- 24 GHz transceiver MMIC (2 TX, 2 RX)
- Fully integrated low phase noise VCO
- Medium power amplifier with variable output power
- Integrated power detectors
- Homodyne low noise quadrature receivers
- Configurable analog baseband amplification stages
- Frequency divider
- Low power consumption
- Multimode operation (Master/Slave)
- Fully ESD protected device
- Single ended RF terminals
- Single supply voltage 1.5V
- WFWLB-52-3 pin plastic package sized 3.63mmx3.63mm
- Pb-free (RoHS compliant) package



Potential Applications

- Smart home appliances
- Drone collision avoidance
- Traffic monitoring
- Security applications

Description

BGT24LTR22 is a low power, low noise multi-channel Silicon Germanium transceiver MMIC for 24 GHz radar applications. It provides building blocks for analog signal generation and reception, operating in the frequency range from 24.0 GHz up to 24.25 GHz. Integrated digital blocks controlling the chip are implemented in order to support radar system design.

The device is manufactured in Infineon's B11HFC BiCMOS technology offering a cutoff frequency higher than 300GHz. It is housed in Infineon's plastic embedded Wafer Level Ball Grid Array (eWLB) package which can be processed in standard SMT flow.



Table of Content

Features 1

Potential Applications..... 1

Description 1

Table of Content 2

1 Electrical Characteristics 3

1.1 Absolute Maximum Ratings 3

1.2 ESD Integrity 4

1.3 Power Supply..... 4

1.4 TX Section 4

1.5 RX Section 5

1.6 Frequency Divider 6

2 SPI Interface..... 7

2.1 SPI Timing Requirements..... 7

3 Block Diagram and Pin Description..... 8

3.1 Block Diagram 8

3.2 Pin Out 9

3.3 Pin Definition and Function 9

4 Package Dimensions and Footprint 11

Electrical Characteristics

1 Electrical Characteristics

Attention: Test ■ means that the parameter is not subject to production test. It was verified by design or characterization respectively.

1.1 Absolute Maximum Ratings

Table 1 Absolute Maximum Ratings: $T_A = -40\text{ °C} \dots 85\text{ °C}$; all voltages with respect to ground, positive current flowing into pin (unless otherwise specified)

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|--|--------------|-------|------|--------------------|------|---|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{DD} | -0.3 | - | $V_{DD,max} + 0.3$ | V | |
| DC voltage at RF pins | $V_{DC,RF}$ | 0 | - | 0 | V | DC-short at RF pins (RX1, RX2, TX1, TX2) to GND |
| DC voltage at VCO tuning pin VTUNE | V_{TUNE} | 0 | - | 5 | V | |
| Voltage applied to all other user I/O pins | $V_{DC,I/O}$ | -0.3 | - | $V_{DD} + 0.3$ | V | |
| RF input power RX inputs | P_{RF} | - | - | 0 | dBm | Pins RX1, RX2 |
| Total power dissipation | P_{DISS} | - | - | 500 | mW | |
| Storage temperature range | T_{STG} | -40 | - | 150 | °C | |
| Operational temperature range | T_C | -40 | - | +85 | °C | Temperature at package soldering point |
| Thermal resistance of package | $R_{th,P}$ | - | 18 | - | K/W | Represents bulk silicon to package solder balls |

Attention: Stresses exceeding the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

Electrical Characteristics

1.2 ESD Integrity

Table 2 ESD integrity

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|---------------------------------|---------------|-------|------|------|------|-------------------------|
| | | Min. | Typ. | Max. | | |
| ESD robustness HBM ¹ | $V_{ESD-HBM}$ | -1 | - | 1 | kV | All pins |
| ESD robustness CDM ² | $V_{ESD-CDM}$ | -500 | - | 500 | V | All pins |

1) According to ANSI/ESDA/JEDEC JS-001 (R = 1.5kOhm, C = 100pF) for Electrostatic Discharge Sensitivity Testing, Human Body Model (HBM)-Component Level

2) According to ESDA/JEDEC JS-002 Field-Induced Charged Device Model (CDM), Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components

Please note that this result is subject to:

- lot variations within the manufacturing process as specified by Infineon
- changes in the specific test setup

1.3 Power Supply

Table 3 Power Supply Electrical Characteristics: $T_A = -40\text{ °C} \dots 85\text{ °C}$

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|--|-----------------|-------|------|------|------|----------------------------------|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{DD} | 1.45 | 1.5 | 1.6 | V | |
| Supply current nominal operation mode | I_{DD_ON} | - | 170 | 230 | mA | SPI Settings – Refer to UG172630 |
| Supply current in reduced power consumption mode | I_{DD_RED} | - | 135 | - | mA | SPI Settings – Refer to UG172630 |
| Supply current standby-mode | I_{DD_STDBY} | - | - | 1 | mA | SPI Settings – Refer to UG172630 |

1.4 TX Section

Table 4 TX Section Electrical Characteristics: $T_A = -40\text{ °C} \dots 85\text{ °C}$, $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$; all parameters are for master mode operation (unless otherwise specified)

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|---|------------|-------|------------|------------|--------|------------------------------------|
| | | Min. | Typ. | Max. | | |
| VCO frequency range | f_{VCO} | 24.0 | - | 24.25 | GHz | |
| VCO phase noise | P_N | - | -65 -85 | -50 -70 | dBc/Hz | @10kHz offset @100kHz offset |
| VCO AM noise | P_{AM} | - | -148 | - | dBc/Hz | @100kHz offset |
| Tuning voltage to cover VCO frequency range | V_{TUNE} | 0 | 0.7 | 3 | V | ISM band covered from 0 V to 1.5 V |

Electrical Characteristics

Table 4 TX Section Electrical Characteristics: $T_A = -40\text{ }^\circ\text{C} \dots 85\text{ }^\circ\text{C}$, $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$; all parameters are for master mode operation (unless otherwise specified)

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|---|------------------------------|-------|------|------|----------|---|
| | | Min. | Typ. | Max. | | |
| VCO tuning sensitivity within VCO frequency range | $\Delta f / \Delta V_{TUNE}$ | 500 | 1600 | 3000 | MHz/V | |
| VCO temperature drift within VCO frequency range | $\Delta f / \Delta T$ | - | -5 | - | MHz/K | |
| 2 nd Harmonic suppression | $\Delta P_{fund,H2}$ | 15 | 27 | - | dBc | |
| VCO nonharmonic suppression | P_{SPUR} | - | -55 | -40 | dBm | |
| TX output power ¹ | P_{TX1} | 1 | 5 | 9.5 | dBm | |
| TX output power dynamic range | ΔP_{OUT} | 17 | 24 | - | dB | |
| TX load impedance | Z_{TX1} | - | 50 | - | Ω | Single-ended at outer edge of compensation structure on P CB as indicated in UG172630 |

1.5 RX Section

Table 5 RX Section Electrical Characteristics: $T_A = -40\text{ }^\circ\text{C} \dots 85\text{ }^\circ\text{C}$, $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$; all parameters are within master mode operation (unless otherwise specified)

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|---|------------|-------|----------------------------|-------|------|---|
| | | Min. | Typ. | Max. | | |
| RX frequency range | f_{RX} | 24.0 | - | 24.25 | GHz | |
| Single-sideband noise figure ¹ | NF_{SSB} | - | 8 | 16.5 | dB | @ $f_{IF} = 200\text{ kHz}$ – Bypass Mode SPI configurable – Refer to UG172630 |
| | | - | 8.5 | 15.5 | | @ $f_{IF} = 200\text{ kHz}$ – ABB Mode SPI configurable – Refer to UG172630 |
| RF downconverter conversion gain ¹ | G_{DC} | 16 | 25 | 33 | dB | @ $f_{IF} = 200\text{ kHz}$ – Bypass Mode SPI configurable – Refer to UG172630 |
| Analog baseband Gain | G_{ABB} | - | 0/30/35/40/ 45/50/55/60 | - | dB | Configurable via SPI |
| Input 1 dB compression point | IP_{1dB} | - | -19 | - | dBm | RX in Bypass Mode |
| LO input power | P_{LOIN} | - | -10 | - | dBm | For slave mode operation |

¹ Refer to UG172630 for more details about parameter variation over temperature
Datasheet

Electrical Characteristics

Table 5 RX Section Electrical Characteristics: $T_A = -40\text{ }^\circ\text{C} \dots 85\text{ }^\circ\text{C}$, $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$; all parameters are within master mode operation (unless otherwise specified)

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|--|-----------------|-------|--------------|------|------------|--|
| | | Min. | Typ. | Max. | | |
| Baseband high pass filters cut off frequency | F_{c-hpf} | - | 20/50/80/100 | - | kHz | Configurable via SPI 1 st order, -3 dB definition |
| Baseband low pass filters cut off frequency | F_{c-lpf} | - | 600 | - | kHz | 4 th order, -3 dB definition |
| Quadrature phase imbalance | ε_P | -10 | - | 10 | deg | |
| Quadrature amplitude imbalance | ε_A | -1.5 | - | 1.5 | dB | |
| IF output impedance | Z_{IF} | - | 400 | - | Ω | Differential |
| IF output impedance – Bypass Mode | Z_{IFBY} | - | 1 | - | k Ω | Differential |
| IF output common mode voltage | V_{IFCMD} | - | 0.75 | - | V | |
| IF output power supply rejection ratio | $PSRR$ | - | 60 | - | dB | @ DC |
| RX input impedance | Z_{RXIN} | - | 50 | - | Ω | Single-ended at outer edge of compensation structure on PCB as indicated in UG172630 |

1.6 Frequency Divider

Table 6 Frequency Divider Electrical Characteristics: $T_A = -40\text{ }^\circ\text{C} \dots 85\text{ }^\circ\text{C}$, $V_{DD} = 1.45\text{ V} \dots 1.6\text{ V}$,
Freq = 24GHz

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|------------------------------|---------------|-------|-----------------|----------|------|--|
| | | Min. | Typ. | Max. | | |
| Dividing factor 1 | D_{DIV1} | - | 2 ²⁰ | - | - | selectable via SPI |
| Dividing factor 2 | D_{DIV2} | - | 2 ¹⁶ | - | - | selectable via SPI |
| Dividing factor 3 | D_{DIV3} | - | 2 ¹⁴ | - | - | selectable via SPI |
| Dividing factor 4 | D_{DIV4} | - | 2 ¹³ | - | - | selectable via SPI |
| Dividing factor 5 | D_{DIV5} | - | 16 | - | - | selectable via SPI |
| Divider output power | P_{DIV5} | -13 | -5 | 0 | dBm | For dividing factor 5 - @50 Ohms load |
| Divider output voltage range | V_{DIV} | 0 | - | V_{DD} | V | For dividing factors 1 to 4 |
| External capacitive load | $C_{extLoad}$ | - | - | 15 | pF | For dividing factors 1 to 4 |

SPI Interface

2 SPI Interface

2.1 SPI Timing Requirements

The BGT24LTR22 is configured using a 4-wire SPI interface. It is used to configure the internal modules of the BGT24LTR22 chip via registers. The main tasks are to set the mode of operation of the TX and/or RX chain and the baseband section. Communication with an external micro controller is done via the four dedicated pins SPIDI, SPIDO, SPICS and SPICLK. Figure 1 demonstrates how the timing of the SPI behaves. The “working edge” is the rising edge of the clock SPICLK. The master application processor presents data for BGT24LTR22 at the falling edge on SPIDI, BGT24LTR22 samples data at the rising edge. Read data is presented for the master on the rising edge on SPIDO. Refer to the application note UG172630 for all details related to the SPI registers to control the MMIC.

Note: Asynchronous reset (SPIRST) must be de-asserted at least 10 ns before the falling edge of SPICLK.

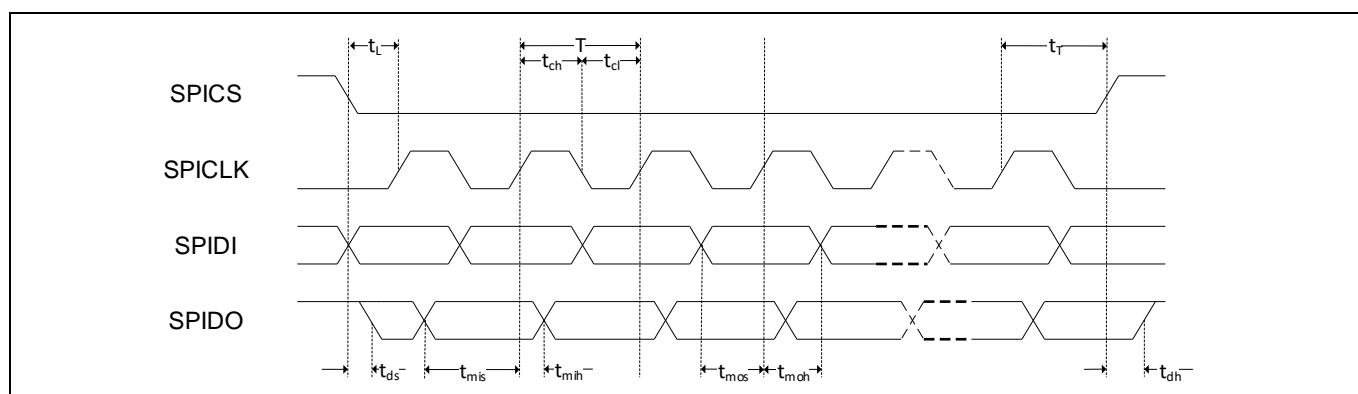


Figure 1 SPI timing diagram

Table 7 SPI Interface timing requirements

| Parameter | Symbol | Values | | | Unit | Note / Test Condition |
|--------------------------------------|---------------------|--------|------|------|------|------------------------------|
| | | Min. | Typ. | Max. | | |
| SPI clock period | T | 20 | | | ns | 50MHz, with <1% clock jitter |
| Clock high time | t_{ch} | 9 | | | ns | |
| Clock low time | t_{cl} | 9 | | | ns | |
| Setup time SPIDI | t_{mos} | 5 | | | ns | |
| Hold time SPIDI | t_{moh} | 5 | | | ns | |
| Setup time SPIDO | t_{mis} | 5 | | | ns | |
| Hold time SPIDO | t_{mih} | 1 | | | ns | |
| Delay time from the output pad logic | $t_{pad_out_dly}$ | | | 5 | ns | |

3 Block Diagram and Pin Description

3.1 Block Diagram

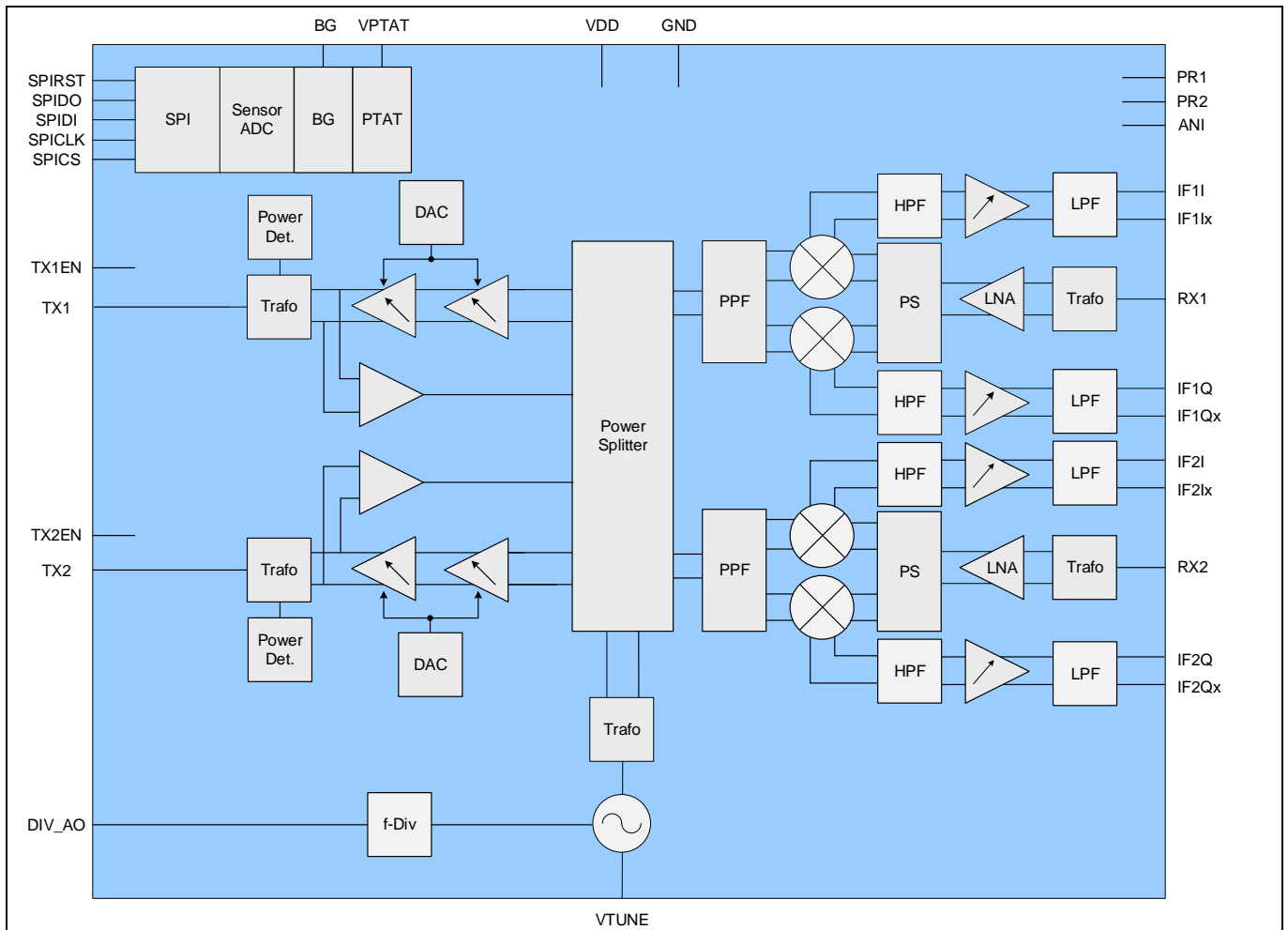


Figure 2 BGT24LTR22 block diagram

3.2 Pin Out

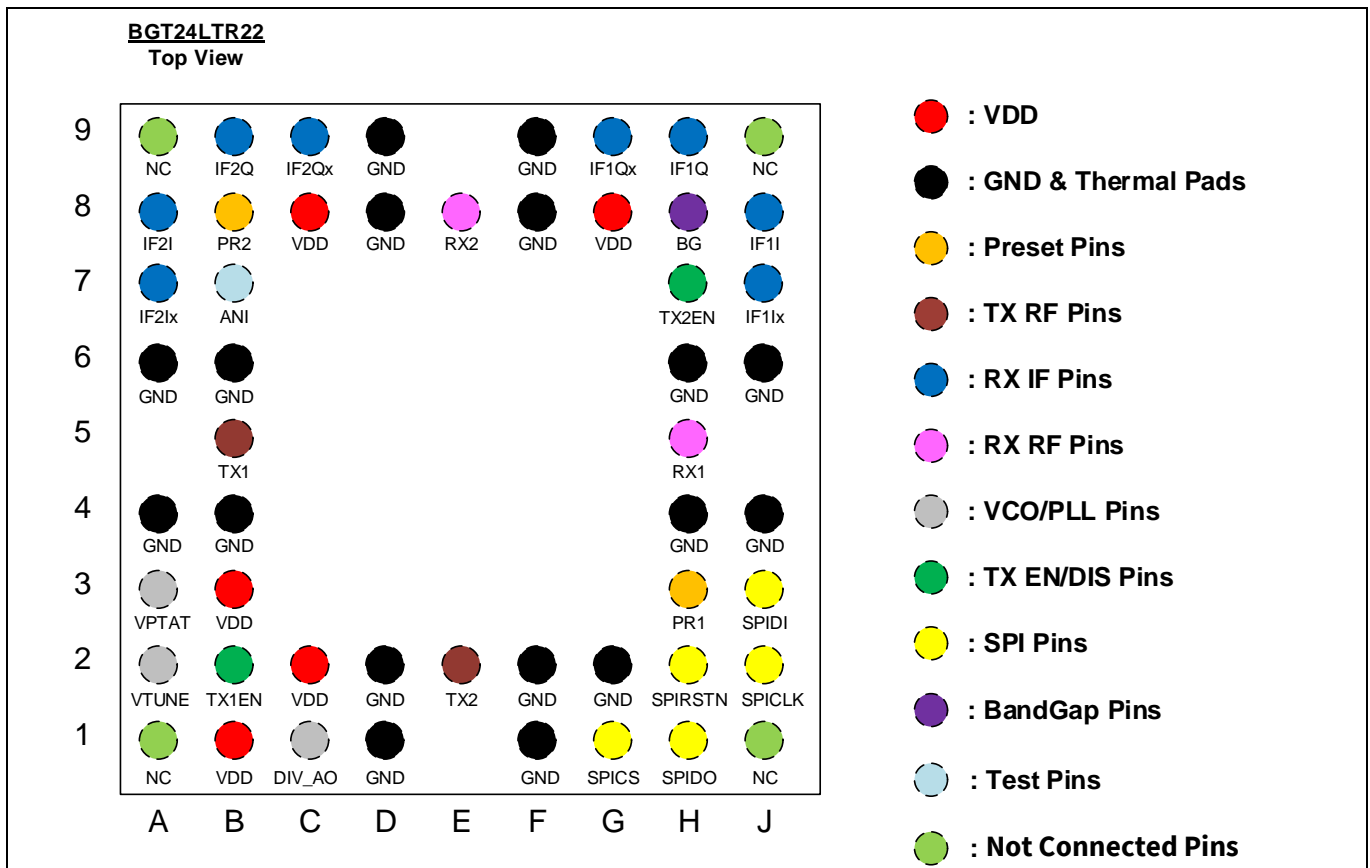


Figure 3 Pin out (top view)

3.3 Pin Definition and Function

Table 8 Pin definition and function

| Pin Number | Name | Function |
|--------------------|-------------|---|
| A1, A9, J1, J9 | NC | No connection |
| B1, B3, C2, C8, G8 | VDD | DC supply voltage |
| H5 | RX1 | RF input - receiver 1 |
| E8 | RX2 | RF input - receiver 2 |
| E2 | TX2 | Bidirectional RF I/O RF output – transmitter 2/LO input 2 |
| B5 | TX1 | Bidirectional RF I/O RF output – transmitter 1/LO input 1 |
| J8, J7 | IF1I, IF1Ix | Complementary in phase downconverter IF output – receiver 1 |
| H9, G9 | IF1Q, IF1Qx | Complementary quadrature phase downconverter IF output - receiver 1 |
| A8, A7 | IF2I, IF2Ix | Complementary in-phase downconverter IF output – receiver 2 |

Table 8 Pin definition and function

| Pin Number | Name | Function |
|---|-------------|---|
| B9, C9 | IF2Q, IF2Qx | Complementary quadrature phase downconverter IF output - receiver 2 |
| A4, A6, B4, B6, D1, D2, D8, D9, F1, F2, F8, F9, G2*, H4, H6, J4, J6 | GND | Ground |
| H3 | PR1 | Mode select - pin 1 |
| B8 | PR2 | Mode select - pin 2 |
| C1 | DIV_AO | Frequency divider output |
| B2 | TX1EN | Enable transmitter 1 |
| H7 | TX2EN | Enable transmitter 2 |
| H8 | BG | Bandgap voltage output |
| A2 | VTUNE | VCO frequency tuning input |
| A3 | VPTAT | PTAT voltage source output |
| G1 | SPICS | SPI chip select (spi_cs_i) |
| H1 | SPIDO | SPI data out (spi_do_o) |
| H2 | SPIRST | SPI reset |
| J2 | SPICLK | SPI clock (spi_clk_i) |
| J3 | SPIDI | SPI data in (spi_di_i) |
| B7 | ANI | Analog input for testing |

Note: *It is mandatory to connect Pin G2 to ground for SPI programming*

4 Package Dimensions and Footprint

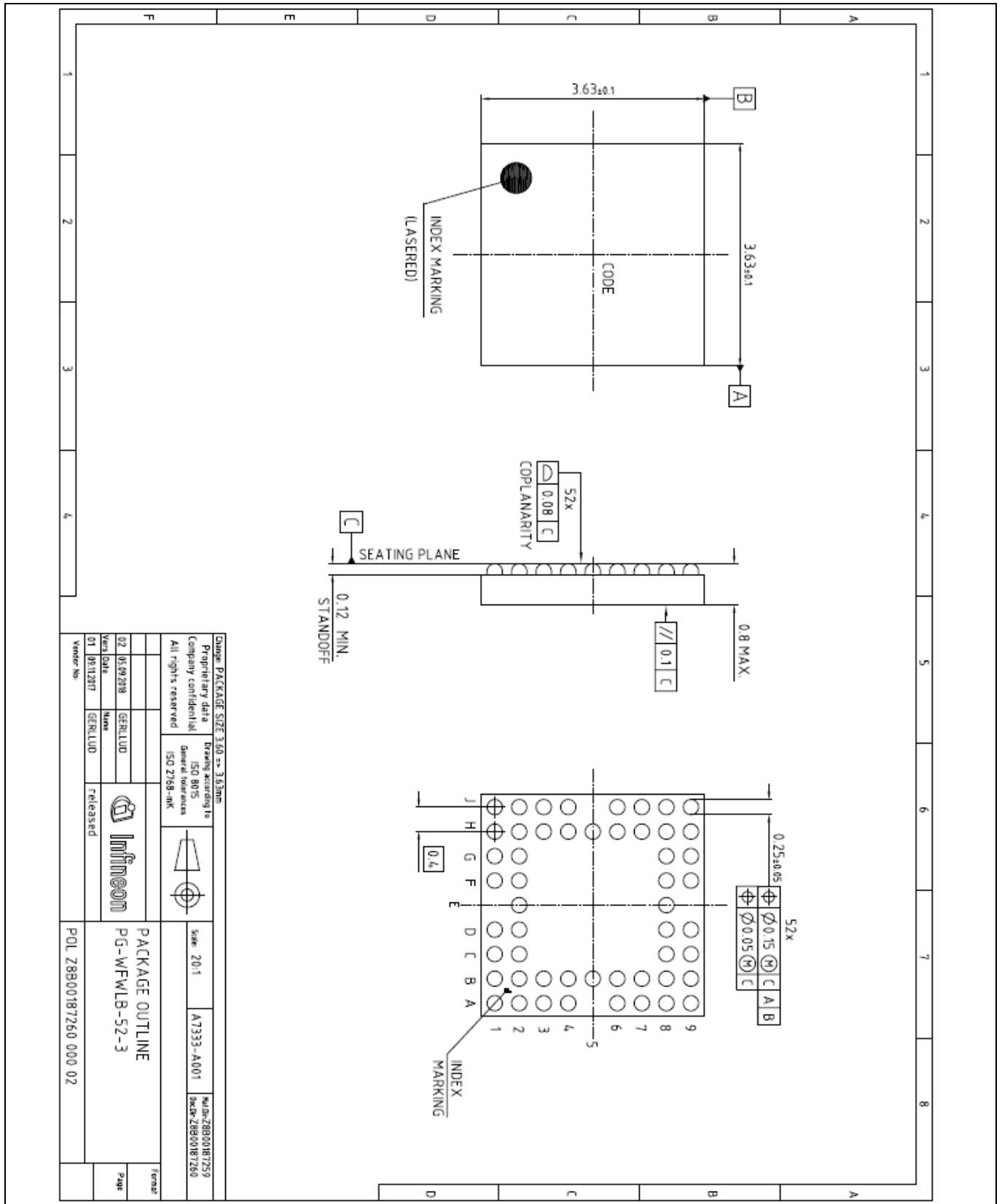


Figure 4 Package outline. Top, side and bottom view of WFWLB-52-3

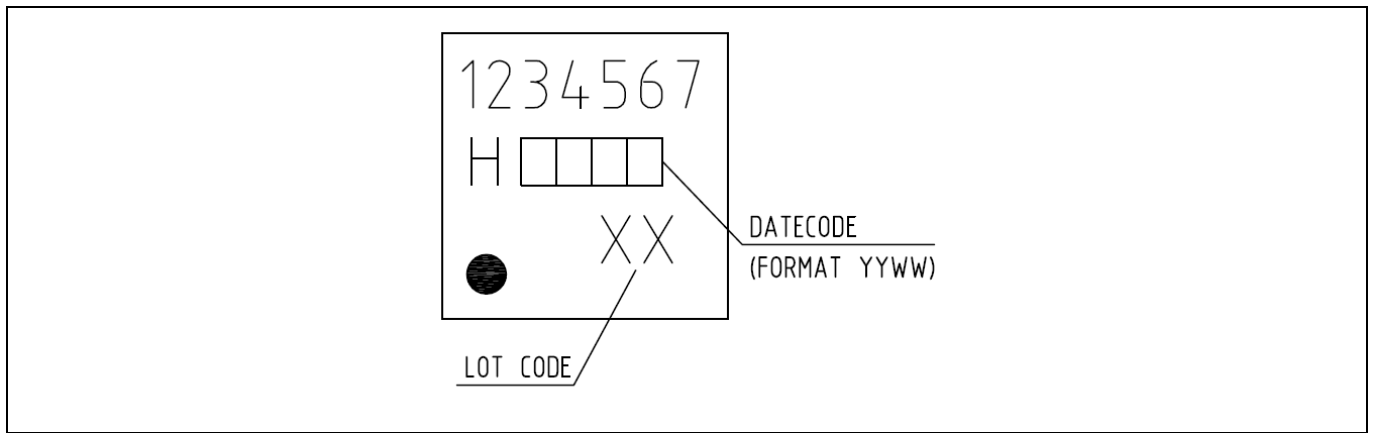


Figure 5 Marking layout of WFWLB-52-3

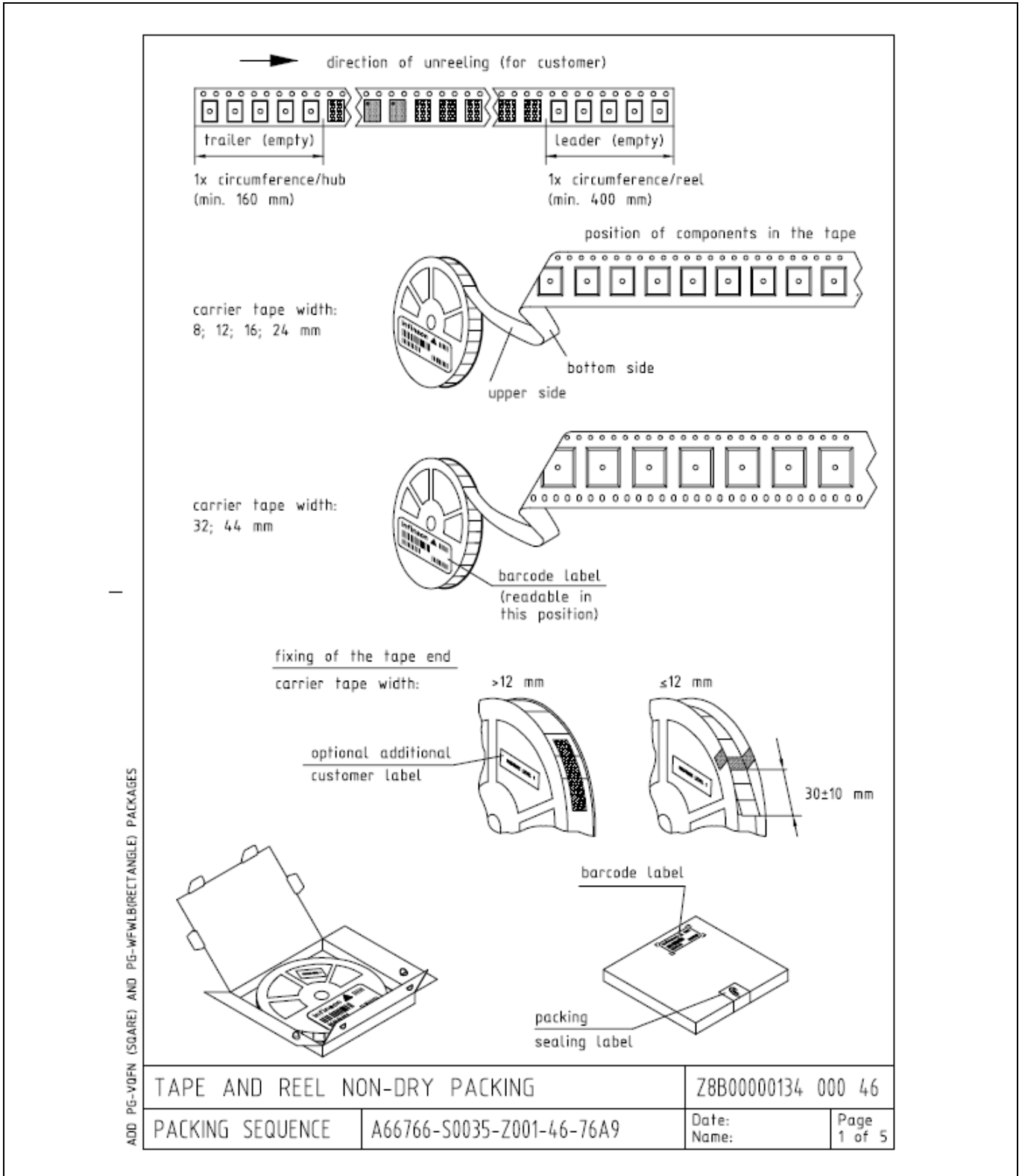


Figure 6 Tape and reel of WFWLB-52-3



Revision history

| Document version | Date of release | Description of changes |
|-------------------------|------------------------|-------------------------------|
| V1.0 | 2020-01-26 | Initial release |
| | | |
| | | |

Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2020-01-26

Published by

Infineon Technologies AG

81726 München, Germany

© 2020 Infineon Technologies AG.

All Rights Reserved.

Do you have a question about this document?

Email: erratum@infineon.com

Document reference

ifx1

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffungsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

For further information on the product, technology delivery terms and conditions and prices please contact your nearest Infineon Technologies office (www.infineon.com).



WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.






Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

-  [View BGT24LTR22E6327XTSA1 on WIN SOURCE](#)
-  [Infineon Technologies Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management